

ABSTRACT

A semiconductor device may include a silicide gate electrode that is disposed over a substrate, a first epitaxial pattern that protrudes from the substrate, a second epitaxial pattern that protrudes from the substrate, a silicide source contact that is connected to the substrate through the first epitaxial pattern and that is disposed at a first level different from a top level of the silicide gate electrode, and a silicide drain contact that is connected to the substrate through the second epitaxial pattern and that is disposed at a second level different from the top level of the silicide gate electrode.

FIG. 1